NGTB20N120IHWG

IGBT − Induction Cooking

This Insulated Gate Bipolar Transistor (IGBT) features a robust and cost effective Field Stop (FS) Trench construction, provides and superior performance in demanding switching applications, and offers low on−state voltage with minimal switching loss. The IGBT is well suited for resonant or soft switching applications.

Features

- Extremely Efficient Trench with Fieldstop Technology
- Low Switching Loss Reduces System Power Dissipation
- Optimized for Low Losses in IH Cooker Application
- This is a Pb−Free Device

Typical Applications

- Inductive Heating
- Consumer Appliances
- Soft Switching

ABSOLUTE MAXIMUM RATINGS

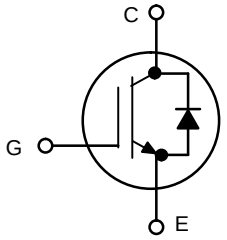
Rating	Symbol	Value	Unit
Collector−emitter voltage @ T_J = 25°C	V_{CES}	1200	V
Collector current @ Tc = 25°C @ Tc = 100°C	I_C	 40 20	A
Pulsed collector current, T_{pulse} limited by T_{Jmax}, 10 μs Pulse, V_{GE} = 15 V	I_{CM}	80	A
Diode forward current @ Tc = 25°C @ Tc = 100°C	I_F	 40 20	A
Diode pulsed current, T_{pulse} limited by T_{Jmax}, 10 μs Pulse, V_{GE} = 0 V	I_{FM}	80	A
Gate−emitter voltage Transient Gate−emitter voltage (T_{pulse} = 5 μs, D < 0.10)	V_{GE}	±20 ±25	V
Power Dissipation @ Tc = 25°C @ Tc = 100°C	P_D	 341 170	W
Operating junction temperature range	T_J	−40 to +175	°C
Storage temperature range	T_{stg}	−55 to +175	°C
Lead temperature for soldering, 1/8″ from case for 5 seconds	T_{SLD}	260	°C

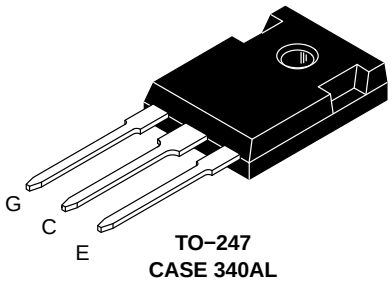
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ON Semiconductor®

www.onsemi.com

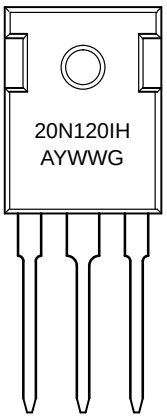
20 A, 1200 V
V_{CEsat} = 2.20 V
E_{off} = 0.48 mJ





TO−247
CASE 340AL

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping
NGTB20N120IHWG	TO−247 (Pb−Free)	30 Units / Rail

© Semiconductor Components Industries, LLC, 2015

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction−to−case	$R_{\theta JC}$	0.44	°C/W
Thermal resistance junction−to−ambient	$R_{\theta JA}$	40	°C/W

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
STATIC CHARACTERISTIC						
Collector−emitter breakdown voltage, gate−emitter short−circuited	V_{GE} = 0 V, I_C = 500 μA	$V_{(BR)CES}$	1200	−	−	V
Collector−emitter saturation voltage	V_{GE} = 15 V, I_C = 20 A V_{GE} = 15 V, I_C = 20 A, T_J = 175°C	V_{CEsat}	− −	2.20 2.30	2.65 −	V
Gate−emitter threshold voltage	V_{GE} = V_{CE}, I_C = 250 μA	$V_{GE(th)}$	4.5	5.5	6.5	V
Collector−emitter cut−off current, gate−emitter short−circuited	V_{GE} = 0 V, V_{CE} = 1200 V V_{GE} = 0 V, V_{CE} = 1200 V, T_J = 150°C	I_{CES}	− −	− −	0.1 2.8	mA
Gate leakage current, collector−emitter short−circuited	V_{GE} = 20 V, V_{CE} = 0 V	I_{GES}	−	−	100	nA
DYNAMIC CHARACTERISTIC						
Input capacitance	V_{CE} = 20 V, V_{GE} = 0 V, f = 1 MHz	C_{ies}	−	3590	−	pF
Output capacitance		C_{oes}	−	90	−	
Reverse transfer capacitance		C_{res}	−	70	−	
Gate charge total	V_{CE} = 600 V, I_C = 20 A, V_{GE} = 15 V	Q_g	−	150	−	nC
Gate to emitter charge		Q_{ge}	−	31	−	
Gate to collector charge		Q_{gc}	−	67	−	
SWITCHING CHARACTERISTIC, INDUCTIVE LOAD						
Turn−off delay time	T_J = 25°C V_{CC} = 600 V, I_C = 20 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(off)}$	−	170	−	ns
Fall time		t_f	−	155	−	
Turn−off switching loss		E_{off}	−	0.48	−	mJ
Turn−off delay time	T_J = 150°C V_{CC} = 600 V, I_C = 20 A R_g = 10 Ω V_{GE} = 0 V/ 15V	$t_{d(off)}$	−	185	−	ns
Fall time		t_f	−	210	−	
Turn−off switching loss		E_{off}	−	0.92	−	mJ
DIODE CHARACTERISTIC						
Forward voltage	V_{GE} = 0 V, I_F = 20 A V_{GE} = 0 V, I_F = 20 A, T_J = 175°C	V_F	− −	2.2 3.8	2.75	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

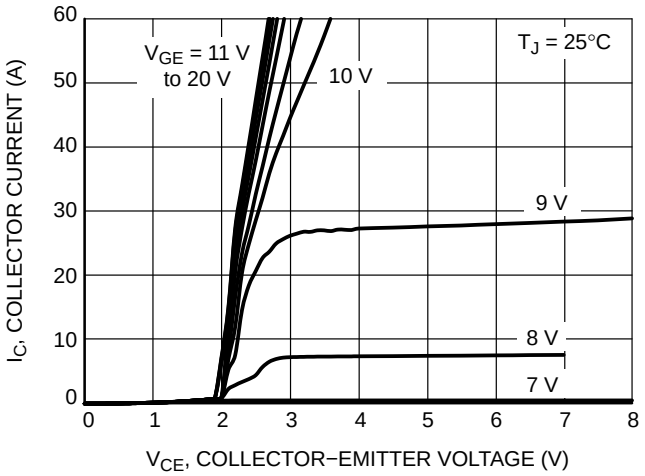


Figure 1. Output Characteristics

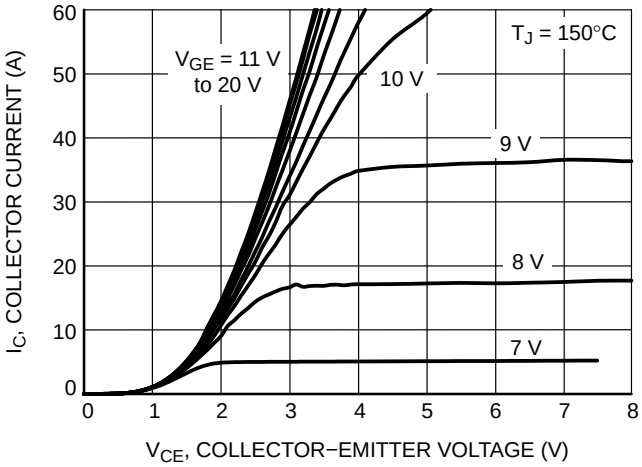


Figure 2. Output Characteristics

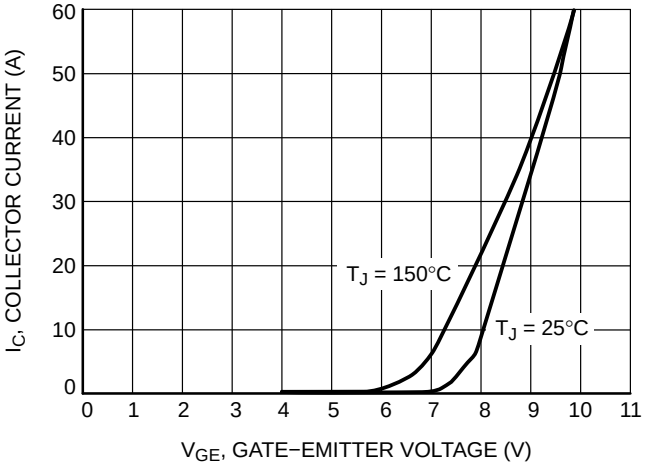


Figure 3. Typical Transfer Characteristics

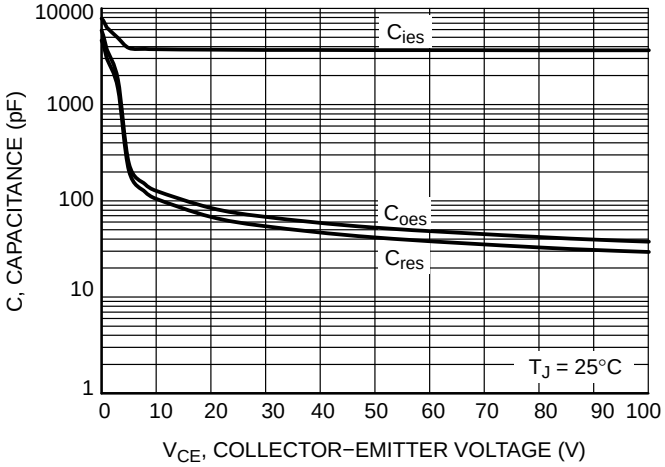


Figure 4. Typical Capacitance

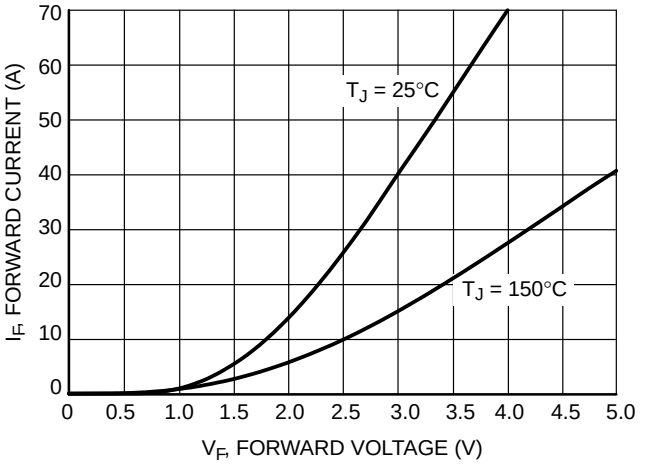


Figure 5. Diode Forward Characteristics

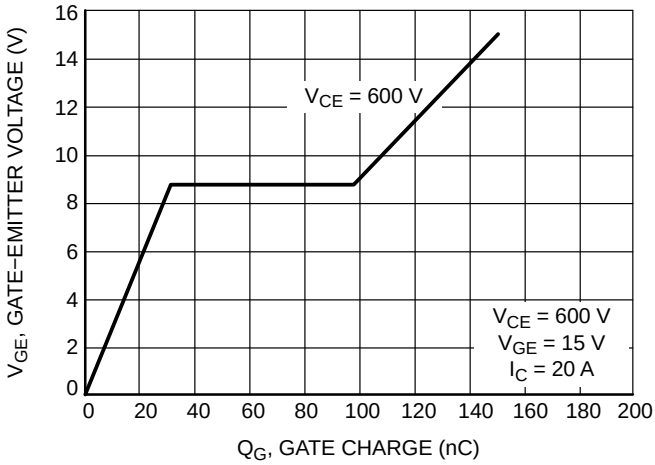


Figure 6. Typical Gate Charge

TYPICAL CHARACTERISTICS

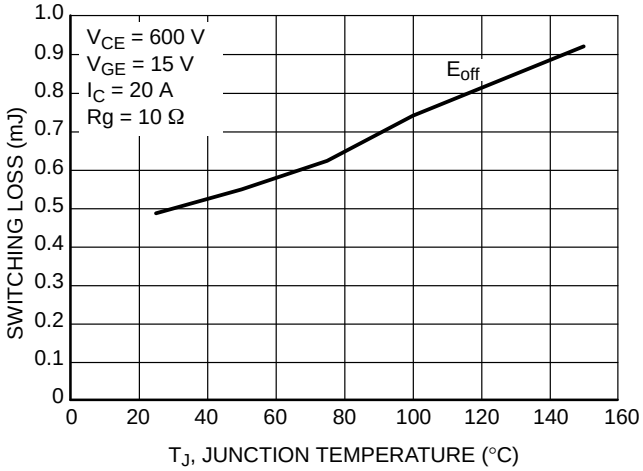


Figure 7. Switching Loss vs. Temperature

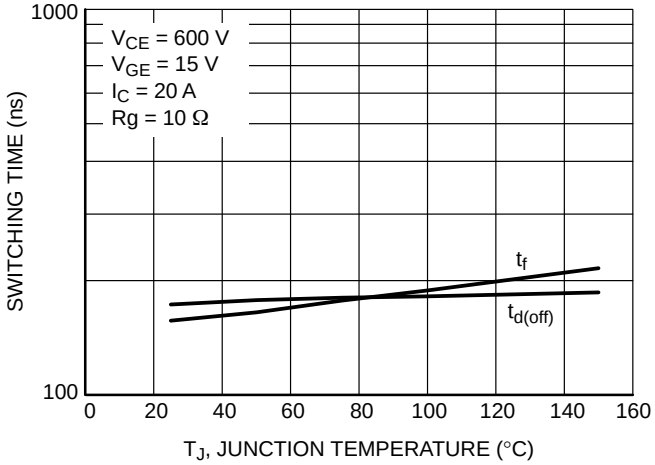


Figure 8. Switching Time vs. Temperature

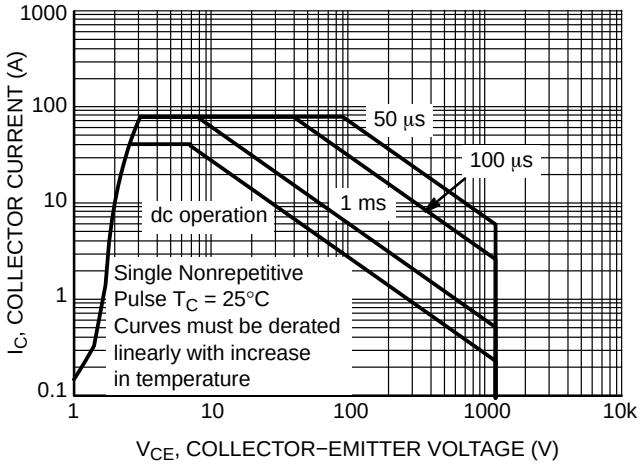


Figure 9. Safe Operating Area

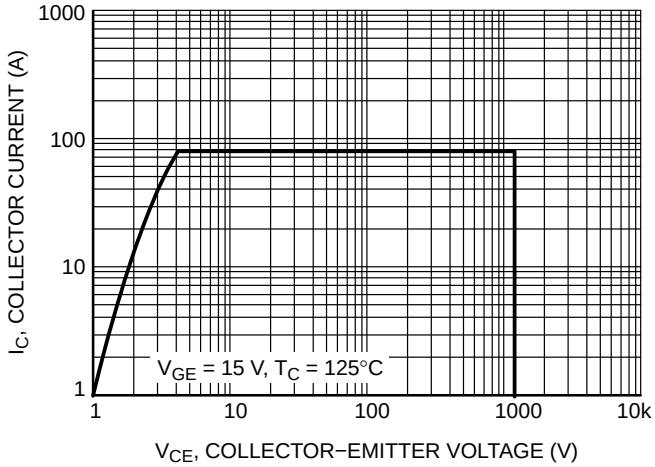
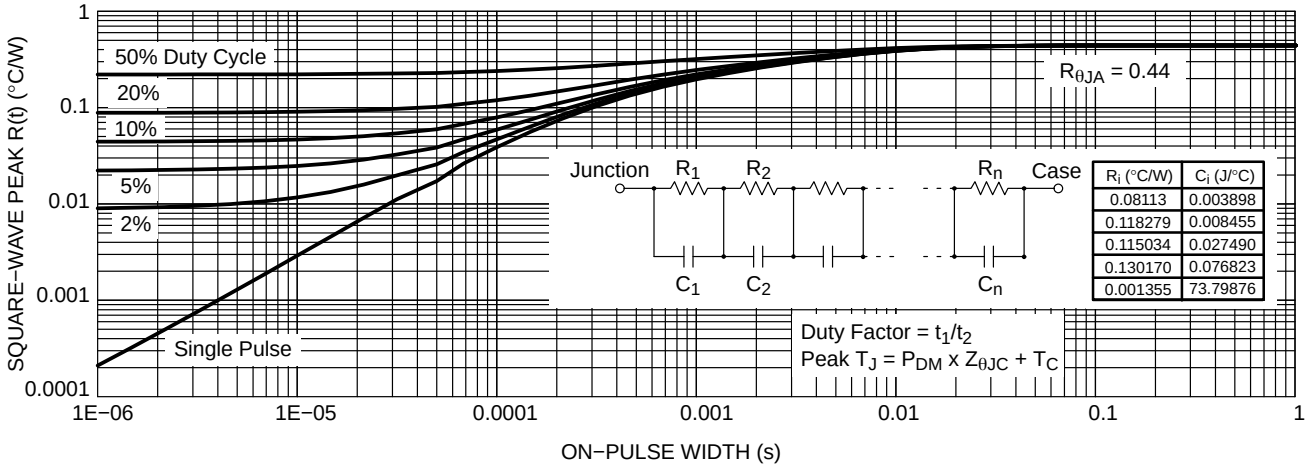


Figure 10. Reverse Bias Safe Operating Area



R_i (°C/W)	C_i (J/°C)
0.08113	0.003898
0.118279	0.008455
0.115034	0.027490
0.130170	0.076823
0.001355	73.79876

Figure 11. IGBT Transient Thermal Impedance

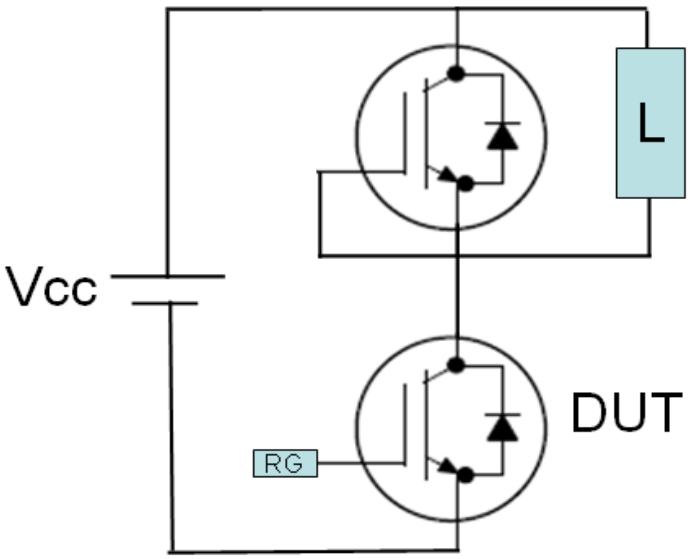


Figure 12. Test Circuit for Switching Characteristics

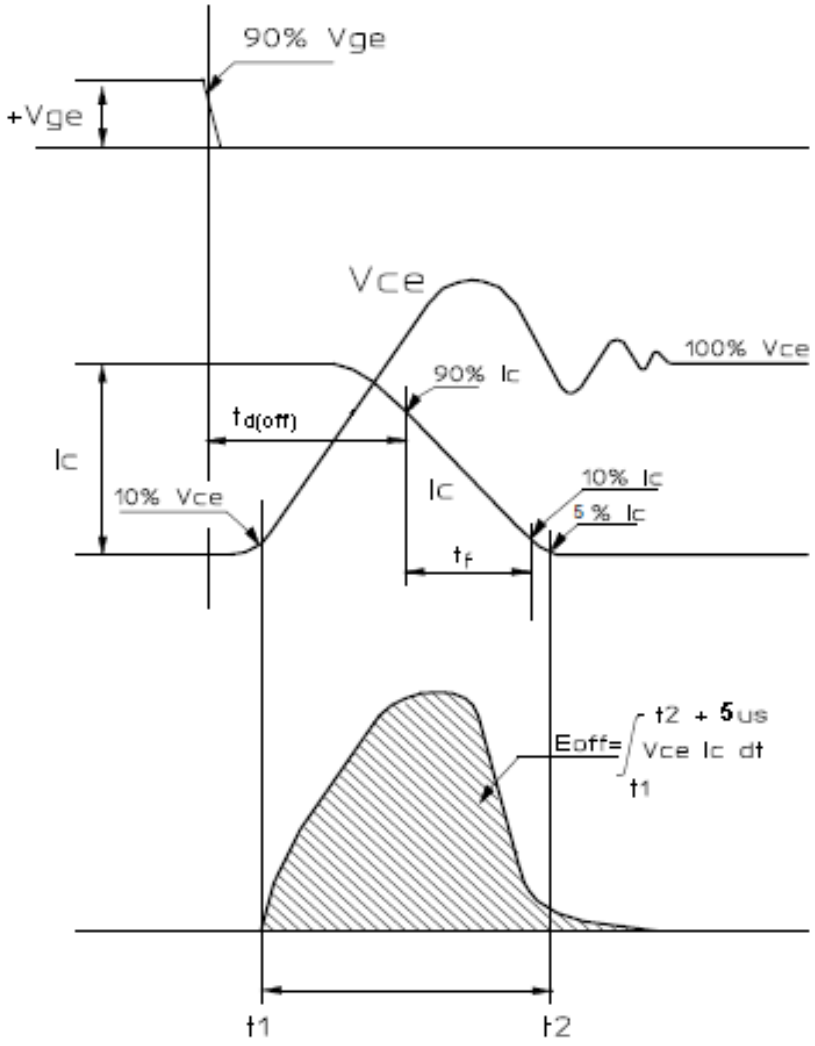
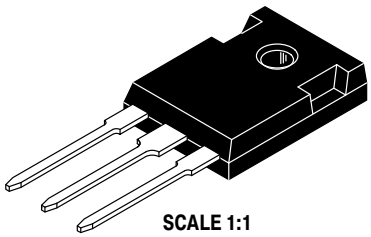


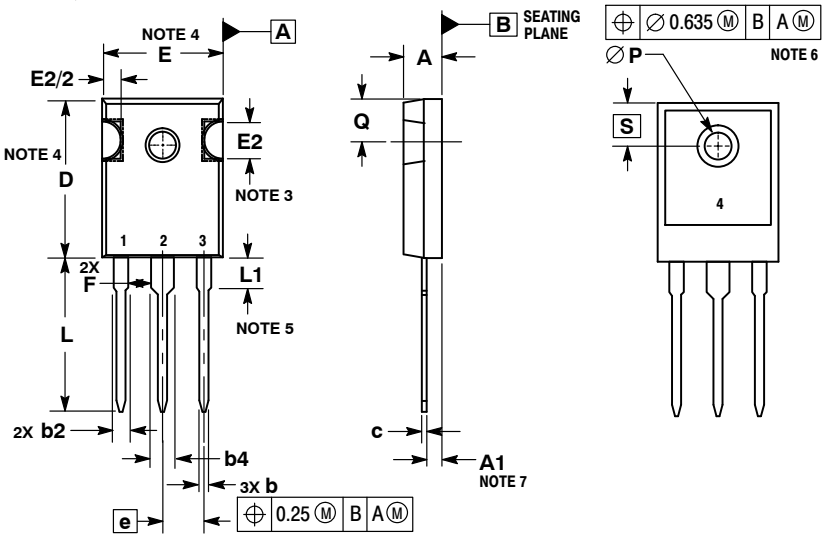
Figure 13. Definition of Turn Off Waveform

TO−247
CASE 340AL
ISSUE D

DATE 17 MAR 2017



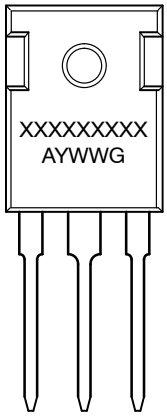
SCALE 1:1



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. SLOT REQUIRED, NOTCH MAY BE ROUNDED.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREME OF THE PLASTIC BODY.
5. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.
6. ∅P SHALL HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM DIAMETER OF 3.91.
7. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.

	MILLIMETERS	
DIM	MIN	MAX
A	4.70	5.30
A1	2.20	2.60
b	1.07	1.33
b2	1.65	2.35
b4	2.60	3.40
c	0.45	0.68
D	20.80	21.34
E	15.50	16.25
E2	4.32	5.49
e	5.45 BSC	
F	2.655	---
L	19.80	20.80
L1	3.81	4.32
P	3.55	3.65
Q	5.40	6.20
S	6.15 BSC	

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking.
Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present.

DOCUMENT NUMBER:	98AON16119F	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	TO−247	PAGE 1 OF 1

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at
www.onsemi.com/support/sales